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| Substitute for form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(Use as many sheets as necessary)</i> | | Complete if Known | | | | |
| | | Application Number | Unknown | | | |
| | | Filing Date | Even Date Herewith | | | |
| | | First Named Inventor | Forbes, Leonard | | | |
| | | Group Art Unit | Unknown | 2824 | | |
| | | Examiner Name | Unknown | Hien Nguyen | | |
| Sheet 1 of 1 | | Attorney Docket No: 303.620US2 | | | | |

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EXAMINER

Hien Nguyen

DATE CONSIDERED

3/19/04